

SINGLE CHANNEL IL30/31/55 DUAL CHANNEL ILD30/31/55 QUAD CHANNEL ILQ30/31/55 PHOTODARLINGTON OPTOCOUPLER

FEATURES

- Current Transfer Ratio
IL/ILD/ILQ30/55, 100% min.
IL/ILD/ILQ31, 200% min.
- 125 mA Load Current Rating
- Fast Rise Time, 10 μ S
- Fast Fall Time, 35 μ S
- Single, Dual and Quad Channel
- Solid State Reliability
- Standard DIP Packages
- Underwriters Lab File #E52744
-  VDE 0884 Available with Option 1

DESCRIPTION

The IL30/31/55, ILD30/31/55, and ILQ30/31/55 are optically coupled isolators with Gallium Arsenide infrared emitters and silicon photodarlington sensors. Switching can be achieved while maintaining a high degree of isolation between driving and load circuits, with no crosstalk between channels. These optocouplers can be used to replace reed and mercury relays with advantages of long life, high speed switching and elimination of magnetic fields.

The IL30/31/55 are equivalent to MCA230/MCA231/MCA255. The ILD30/31/55 re designed to reduce board space requirements in high density applications.

Maximum Ratings

Emitter (each channel)

Peak Reverse Voltage	3 V
Continuous Forward Current	60 mA
Power Dissipation at 25°C	100 mW
Derate Linearly from 25°C	1.33 mW/°C

Detector (each channel)

Collector-Emitter Breakdown Voltage	
IL/D/Q30	30 V
IL/D/Q55	55 V

Collector (Load) Current	125 mA
Power Dissipation at 25°C Ambient	150 mW
Derate Linearly from 25°C	2.0 mW/°C

Package

Total Package Power Dissipation at 25°C

IL30/31/55	250 mW
ILD30/31/55	400 mW
ILQ30/31/55	500 mW

Derate Linearly from 25°C

IL30/31/55	3.3 mW/°C
ILD30/31/55	5.33 mW/°C
ILQ30/31/55	6.67 mW/°C

Isolation Test Voltage 5300 VAC_{RMS}

Creepage 7 mm min.

Clearance 7 mm min.

Comparative Tracking Index 175

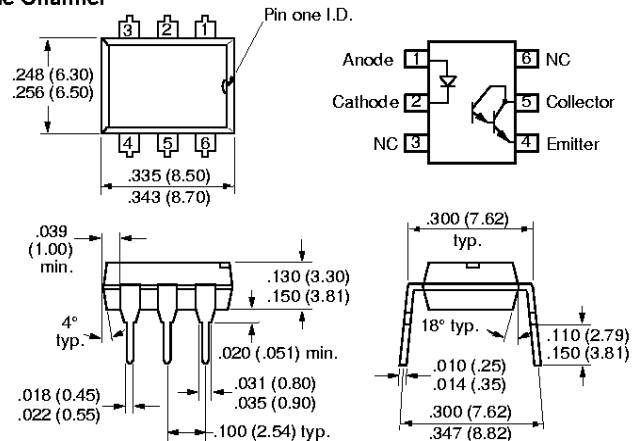
Storage Temperature -55°C to +125°C

Operating Temperature -55°C to +100°C

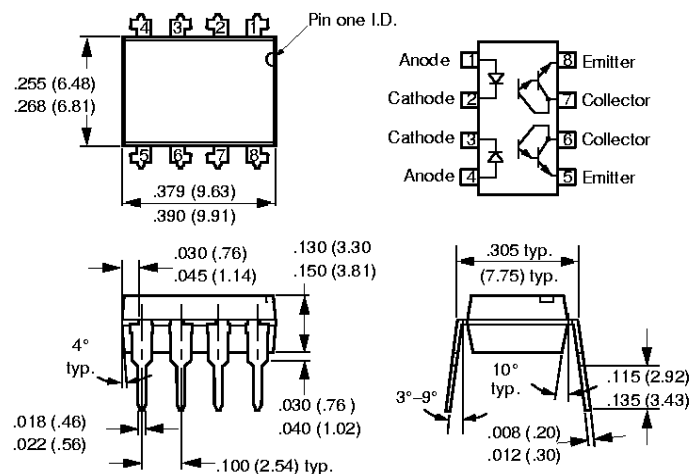
Lead Soldering Time at 260°C 10 sec.

Dimensions in inches (mm)

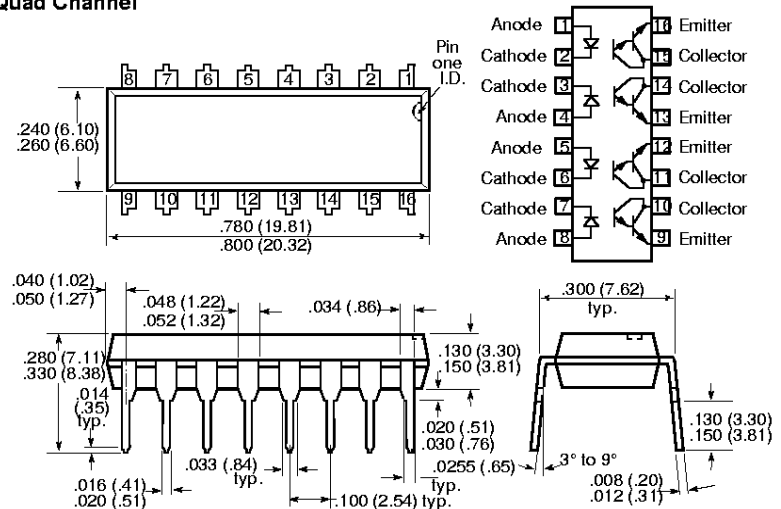
Single Channel



Dual Channel



Quad Channel



Electrical Characteristics (T_A=25°C)

	Symbol	Min.	Typ.	Max..	Unit	Condition
GaAs Emitter (per channel)						
Forward Voltage	V _F		1.25	1.5	V	I _F =20 mA
Reverse Current	I _R		0.1	10	μA	V _R =3.0 V
Capacitance	C _O		25		pF	V _R =0 V
Detector (per channel)						
Collector-Emitter Breakdown Voltage	BV _{CEO}	30/55			V	I _C =100 μA
Collector-Emitter Leakage Current	I _{CEO}		1.0	100	nA	V _{CE} =10 V, I _F =0
Collector-Emitter Capacitance	C _{CE}		3.4		pF	V _{CE} =10 V, f=1 MHz
Package						
Current Transfer Ratio IL/D/Q30/55 IL/D/Q31	CTR	100 200	400 400		% %	I _F =10 mA, V _{CE} =5 V I _F =10 mA, V _{CE} =5 V
Collector-Emitter Saturation Voltage	V _{CEsat}		0.9	1.0	V	I _C =50 mA, I _F =50 mA
Isolation Test Voltage		5300			VAC _{RM} S	
Isolation Resistance	R _{ISOL}		10 ¹²		W	
Coupling Capacitance	C _{ISOL}		0.5		pF	
Rise Time	t _R		10		μs	V _{CC} =13.5 V, I _F =50 mA, R _L =100 Ω
Fall Time	t _F		35		μs	

Figure 1. Forward voltage versus forward current

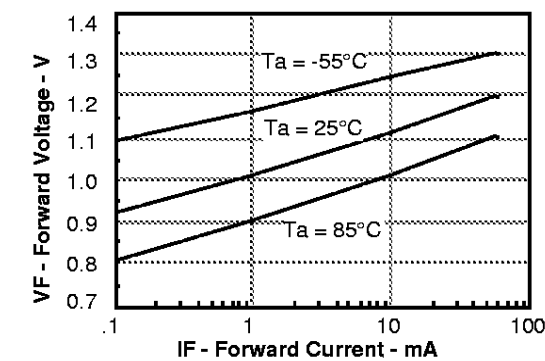


Figure 2. Normalized non-saturated and saturated CTR_{ce} at T_A=25°C versus LED current

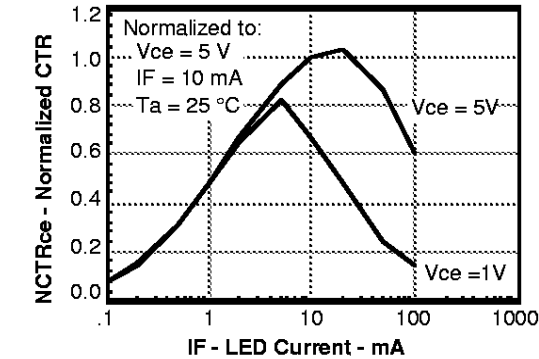


Figure 3. Normalized non-saturated and saturated collector-emitter current versus LED current

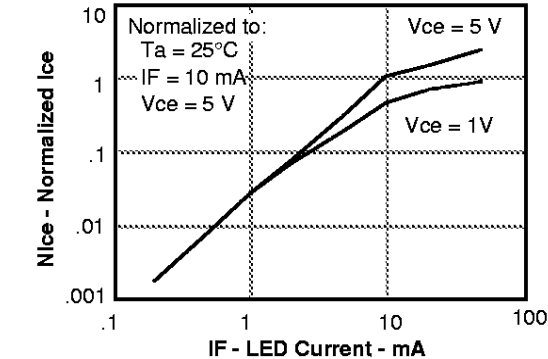


Figure 4. Normalized collector-base photocurrent versus LED current

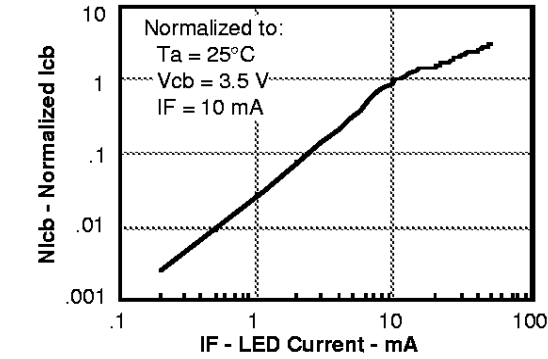


Figure 5. Hfe current gain versus base current

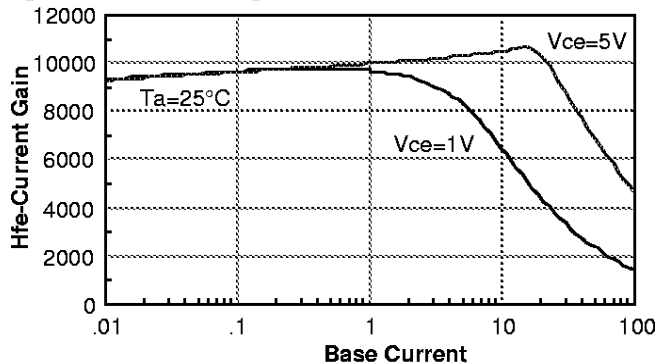


Figure 6. Low to high propagation delay versus collector load resistance and LED current

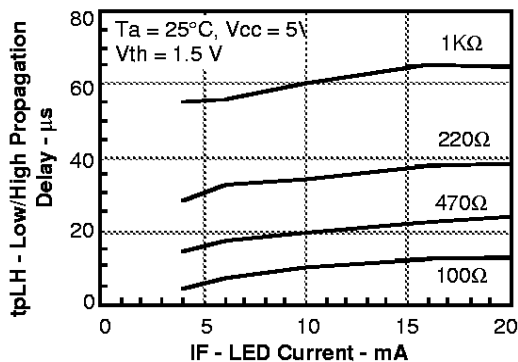


Figure 7. High to low propagation delay versus collector load resistance and LED current

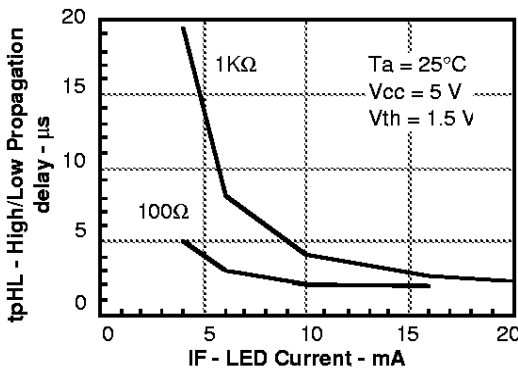


Figure 8. Switching waveforms

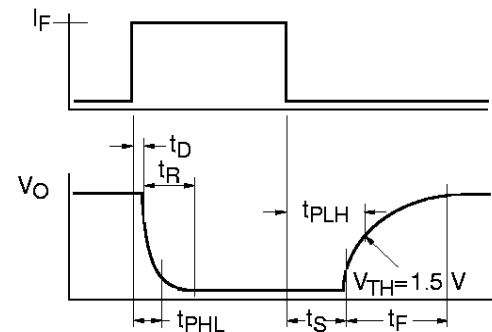


Figure 9. Switching schematic

